

AMENDMENTS TO THE CLAIMS

The following listing of claims replaces all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor structure, comprising:

a substrate;

a buffer layer formed on the substrate;

a first layer formed above the [substrate] buffer layer; and

a textured nitride layer formed on the first layer.

2. (Original) The structure of claim 1, further comprising at least one of: a dielectric layer and a metal layer formed above the textured nitride layer.

3. (Canceled)

4. (Currently Amended) The structure of claim [3] 1, further comprising at least one of: a GaN layer and an AlInGaN layer formed between the buffer layer and the first layer.

5. (Currently Amended) The structure of claim 1, further comprising a light emitting structure formed between the [substrate] buffer layer and the first layer.

6. (Original) The structure of claim 1, wherein the structure is used as a semiconductor device comprising at least one of: a field effect transistor, a light emitting diode, and a laser.

7. (Original) The structure of claim 1, wherein the first layer comprises a crystalline nitride layer.

8. (Currently Amended) The structure of claim 1, wherein the textured nitride layer partially covers the first [layer] layer.

9. (Original) The structure of claim 8, wherein the textured nitride layer forms at least one of: a stripe pattern and a circle pattern.

10. (Currently Amended) The structure of claim [7] 1, wherein the first layer and the textured nitride layer comprise a gate barrier structure.

11. (Original) The structure of claim 10, further comprising at least one contact formed on the gate barrier structure.

12. (Original) A field effect transistor comprising:

a substrate;

an active layer formed above the substrate;

a crystalline nitride layer formed above the active layer; and

a textured nitride layer formed on the crystalline nitride layer.

13. (Original) The field effect transistor of claim 12, wherein the crystalline nitride layer and the textured nitride layer comprise a gate barrier structure.

14. (Original) The field effect transistor of claim 13, further comprising at least one of: a source contact, a drain contact, and a gate contact formed above the textured nitride layer.

15. (Original) The field effect transistor of claim 12, further comprising at least one of: a source contact, a drain contact, and a gate contact formed beside the textured nitride layer.

16. (Original) The field effect transistor of claim 12, wherein the nitride layer forms a layered recessed gate structure for at least one of: a source contact, a drain contact, and a gate contact.

17. (Original) The field effect transistor of claim 12, further comprising a passivating layer formed above the textured nitride layer.

18. (Original) A light emitting device, comprising:

a substrate;

an n-type layer formed above the substrate;

a light emitting structure formed above the n-type layer;

a p-type crystalline nitride layer formed above the light emitting structure; and

a textured nitride layer formed on the crystalline nitride layer.

19. (Original) The device of claim 18, further comprising a p-type contact formed above the textured nitride layer.

20. (Original) The device of claim 18, wherein the device comprises at least one of: a light emitting diode and a laser.